

SANYO	No.4765	2SC4919
		NPN Epitaxial Planar Silicon Transistor
Muting Circuit Applications		

Features

- Very small-sized package permitting 2SC4919-applied sets to be made smaller and slimmer.
- Small output capacitance.
- Low collector-to-emitter saturation voltage.
- Small ON resistance.

Absolute Maximum Ratings at Ta = 25°C

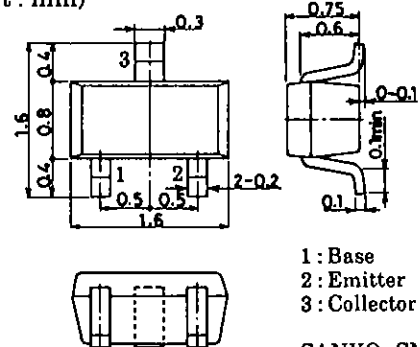
					unit
Collector-to-Base Voltage	V _{CB0}	25			V
Collector-to-Emitter Voltage	V _{CEO}	15			V
Emitter-to-Base Voltage	V _{EBO}	5			V
Collector Current	I _C	100			mA
Collector Current (Pulse)	I _{CP}	200			mA
Base Current	I _B	20			mA
Collector Dissipation	P _C	150			mW
Junction Temperature	T _j	150			°C
Storage Temperature	T _{stg}	-55 to +150			°C

Electrical Characteristics at Ta = 25°C

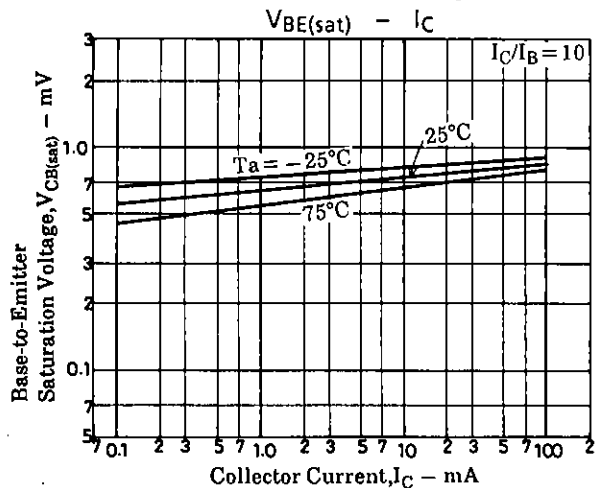
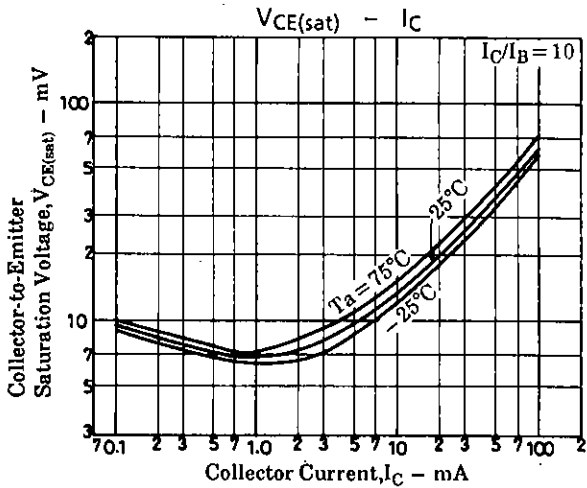
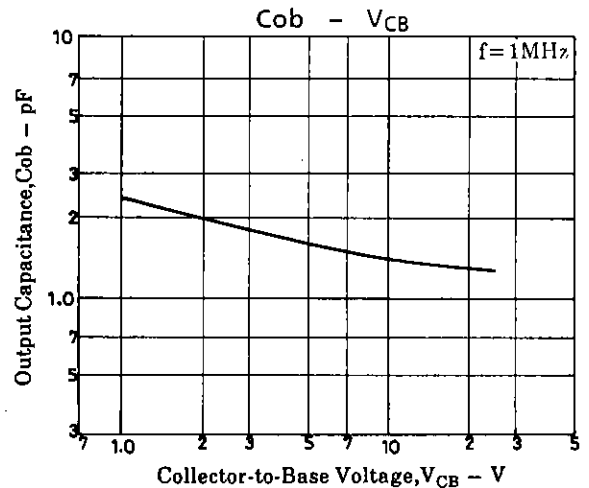
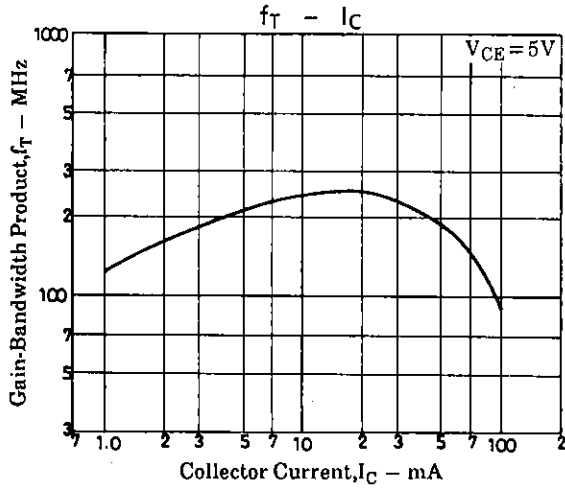
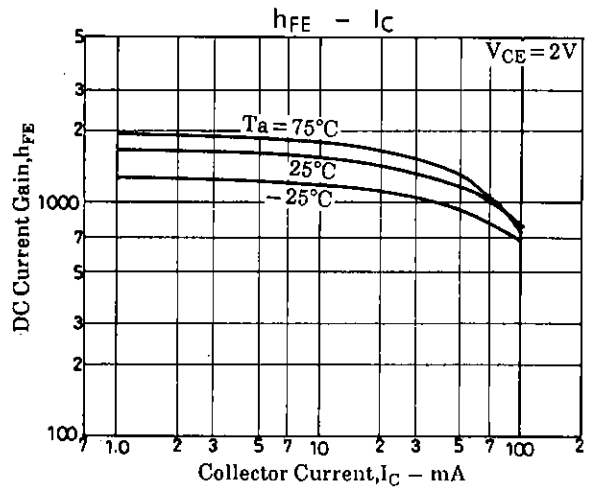
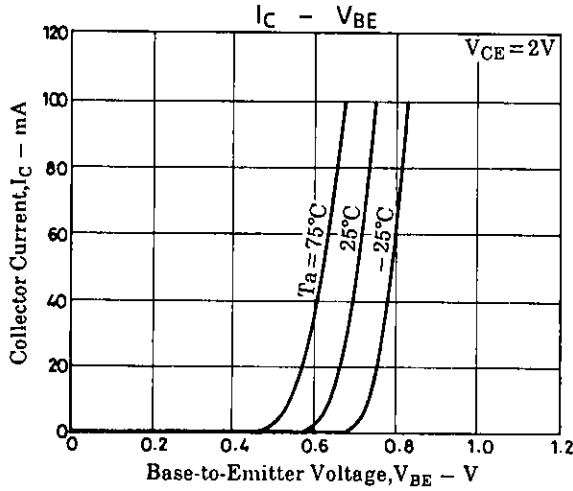
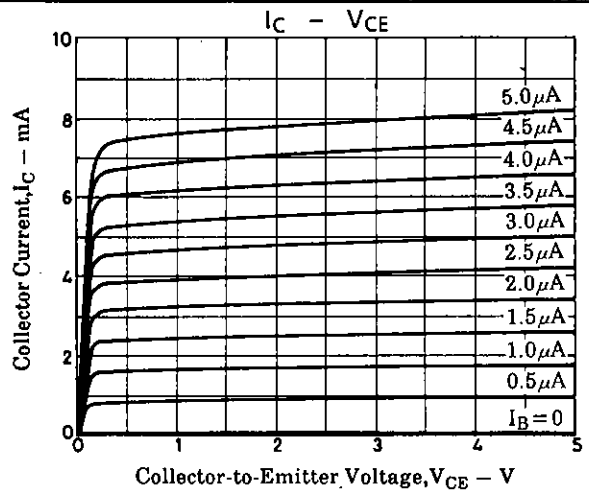
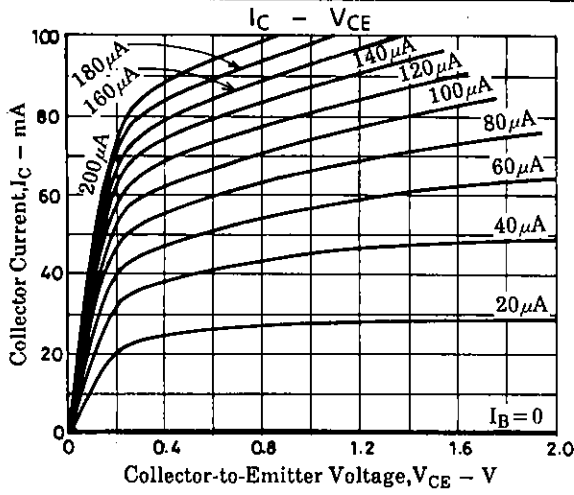
		min	typ	max	unit
Collector Cutoff Current	I _{CB0}	V _{CB} = 15V, I _E = 0		0.1	μA
Emitter Cutoff Current	I _{EBO}	V _{EB} = 4V, I _C = 0		0.1	μA
DC Current Gain	h _{FE}	800		3200	
Gain-Bandwidth Product	f _T		240		MHz
Output Capacitance	C _{ob}	V _{CB} = 10V, f = 1MHz		1.4	pF
C-E Saturation Voltage	V _{CE(sat)}	I _C = 10mA, I _B = 1mA		14	30 mV
B-E Saturation Voltage	V _{BE(sat)}	I _C = 10mA, I _B = 1mA		0.74	1.1 V
C-B Breakdown Voltage	V _{(BR)CBO}	I _C = 10μA, I _E = 0		25	V
C-E Breakdown Voltage	V _{(BR)CEO}	I _C = 1mA, R _{BE} = ∞		15	V
E-B Breakdown Voltage	V _{(BR)EBO}	I _E = 10μA, I _C = 0		5	V
ON Resistance	R _{on}	I _B = 3mA, f = 1MHz		0.9	Ω

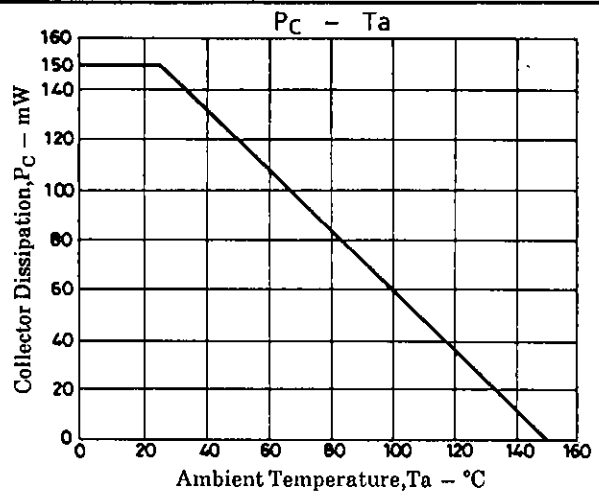
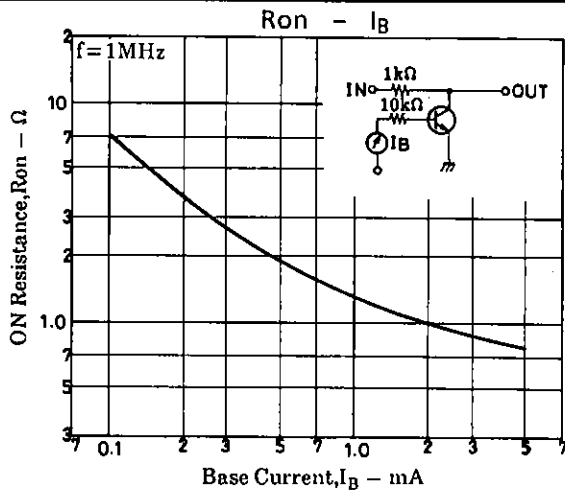
Marking : DA

Package Dimensions 2106A
(unit : mm)



SANYO : SMCP





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